

Update of Search 8/6/4 ~~13pp.~~ (13pp.)

L Number	Hits	Search Text	DB	Time stamp
1	676	257/499	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:05
2	79	257/504	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:05
3	1511	257/506	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:05
4	1093	257/510	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:06
5	437	257/517	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:06
6	434	257/520	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:06
7	292	257/509	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:06
8	487	257/513	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:06
9	1105	257/329	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:07
10	1620	257/330	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:07
11	674	257/332	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:07
12	6269	257/499 257/504 257/506 257/510 257/517 257/520 257/509 257/513 257/329 257/330 257/332	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:08
13	240	(257/499 257/504 257/506 257/510 257/517 257/520 257/509 257/513 257/329 257/330 257/332) and epitax\$5 and (trench groove) near6 (isolat\$3 insulat\$3) and (bipolar bcd bipolar-cmos-dmos) and plan adj view (("4416050") or ("5476809") or ("5597742")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:10
-	9		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/06 16:05

-	3	((("4416050") or ("5476809") or ("5597742")) . PN.	USPAT	2002/04/15 12:59
-	0	jp-63-293938\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/04/15 12:54
-	2	jp-63293938\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/04/15 12:54
-	0	ep-0292972\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/04/15 13:00
-	2	ep-292972\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/04/15 13:01
-	2	ep-429131\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/04/15 13:02
-	2	ep-566186\$--.did.	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/04/15 13:31
-	121	(257/499).CCLS.	USPAT; US-PGPUB	2002/04/15 13:41
-	555	(257/506).CCLS.	USPAT;	2002/04/15 13:41
-	126	(257/509).CCLS.	USPAT; US-PGPUB	2002/04/15 13:41
-	183	(257/520).CCLS.	USPAT; US-PGPUB	2002/04/15 13:41
-	654	(((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/04/15 13:54
-	341	((((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and surround\$3	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/04/15 14:03
-	66	((((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and (surround\$3 near12 transistor)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2003/05/31 18:59
-	1	(((((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and (surround\$3 near12 transistor)) and inductive adj load	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/04/15 14:06
-	1	(((((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and (surround\$3 near12 transistor)) and (power adj transistor near12 (inductive adj load or induction or inductor))	US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT;	2002/04/15 14:07

-		1	((((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and (surround\$3 near12 transistor)) and (power adj transistor near12 (inductive adj load or induction or inductor or inductance))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 14:09
-		3	((((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and (surround\$3 near12 transistor)) and (transistor near12 (inductive adj load or induction or inductor or inductance))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 14:09
-		337	(257/510).CCLS.	USPAT;	2002/04/15 14:44
-		0	(257/510 and ((trench or groove) near12 (polysilicon or poly-si or polysilicon)) near12 dielectric).CCLS.	USPAT; US-PGPUB	2002/04/15 14:46
-		0	(257/510 and ((trench or groove) near12 (polysilicon or poly-si or polysilicon)) near12 (dielectric or liner or lining)).CCLS.	USPAT; US-PGPUB	2002/04/15 14:46
-		1067	((trench or groove) near12 (polysilicon or poly-si or polysilicon)) near12 (dielectric or liner or lining)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 14:47
-		689	((trench or groove) near6 (polysilicon or poly-si or polysilicon)) near6 (dielectric or liner or lining)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 14:53
-		37	((trench or groove) near6 (polysilicon or poly-si or polysilicon)) near6 (dielectric or liner or lining) and device adj isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 17:17
-		9	((trench or groove) near12 (device adj isolation)) same transistor) and ((polysilicon or poly-silicon or poly-si) near12 (trench or groove) near12 (lining or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 17:23
-		158	((trench or groove) near12 isolat\$3) near12 transistor) and ((polysilicon or poly-silicon or poly-si) near12 (trench or groove) near12 (lining or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:43
-		0	"n<sb>+<sb>" adj "n<sb>-<sb>" same substrate same epitaxial same trench same polysilicon same dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:51
-		0	"n.sub.+" adj "n.sub.-" same substrate same epitaxial same trench same polysilicon same dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:52
-		45	erratico.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:53
-		0	("n+n-" or "p+p-") same substrate same epitaxial same (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:54

-	5	("n+n-" or "p+p-") and substrate and epitaxial and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:54
-	3	("n+n-" or "p+p-") and substrate and epitaxial and (trench or groove) and polysilicon and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:58
-	5	("n+n-" or "p+p-") and substrate and epitaxial and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 19:09
-	5	("n+n-" or "p+p-") and epitaxial and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 19:10
-	48	("n+n-" or "p+p-") and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 19:10
-	2	("6184565").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 09:22
-	1676	epitaxial same substrate same (trench or groove) same isolat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 09:24
-	1173	epitaxial same substrate same (trench or groove) same isolat\$3 and (257/\$6.cccls. or 438/\$6.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 14:26
-	3	("5998822").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 14:03
-	96	epitaxial same substrate same (trench or groove) same isolat\$3 and (257/\$6.cccls. or 438/\$6.cccls.) and power adj2 (device or transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 14:28
-	2	("5990537").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 16:49
-	2	("6184565").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 16:56
-	20	(US-6184566-\$ or US-6204112-\$ or US-5909044-\$ or US-6239465-\$ or US-6133615-\$ or US-5998822-\$ or US-5990537-\$ or US-6184565-\$ or US-5597742-\$ or US-4416050-\$ or US-5476809-\$ or US-5757081-\$ or US-6335556-\$).did. or (US-20010050388-\$ or US-20010012655-\$).did. or (EP-292972-\$ or EP-429131-\$ or EP-566186-\$).did. or (US-5243214-\$ or JP-63293938-\$).did.	USPAT; US-PGPUB; EPO; DERWENT	2002/11/12 11:36

-	12	((US-6184566-\$ or US-6204112-\$ or US-5909044-\$ or US-6239465-\$ or US-6133615-\$ or US-5998822-\$ or US-5990537-\$ or US-6184565-\$ or US-5597742-\$ or US-4416050-\$ or US-5476809-\$ or US-5757081-\$ or US-6335556-\$).did. or (US-20010050388-\$ or US-20010012655-\$).did. or (EP-292972-\$ or EP-429131-\$ or EP-566186-\$).did. or (US-5243214-\$ or JP-63293938-\$).did.) and (vertical or vmos or vmosfet or umos or umosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 08:39
-	3	(trench or sti) near6 width near6 length near6 (die or chip)	USPAT; US-PGPUB; EPO; DERWENT	2002/11/12 11:39
-	335	(257/499).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:40
-	880	(257/506).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:40
-	182	(257/509).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:40
-	251	(257/520).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:40
-	1581	((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/520).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:40
-	149	((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/520).CCLS.) and trench near12 (length or width)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:41
-	23	(US-5476809-\$ or US-6184565-\$ or US-5909044-\$ or US-6204112-\$ or US-5986304-\$ or US-6288431-\$ or US-4661832-\$ or US-6184566-\$ or US-5757081-\$ or US-6335556-\$ or US-5990537-\$ or US-6239465-\$ or US-6133615-\$ or US-5998822-\$ or US-4416050-\$ or US-5597742-\$).did. or (US-20010050388-\$ or US-20010012655-\$).did. or (EP-566186-\$ or EP-429131-\$ or EP-292972-\$).did. or (JP-63293938-\$ or US-5243214-\$).did.	USPAT; US-PGPUB; EPO; DERWENT	2003/02/12 10:40
-	105	LATERAL ADJ TRENCH	USPAT; US-PGPUB; EPO; DERWENT	2003/02/12 10:55
-	97	lateral near6 (mos or mosfet or igfet or nmos or nmosfet or pmos or pmosfet or cmos or cmosfet or field adj effect or fet) and ((trench or groove) near12 gate near12 polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 11:23
-	1217	((257/329) or (257/330) or (257/332)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 11:24

	7	((257/329) or (257/330) or (257/332)).CCLS.) and trench near2 gate near12 separat\$3 near12 source near12 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/31 11:35
	0	((257/329) or (257/330) or (257/332)).CCLS.) and trench near2 gate near12 (polysilicon or polycrystalline adj silicon) near12 separat\$3 near12 source near12 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 11:28
	86	((257/329) or (257/330) or (257/332)).CCLS.) and trench near2 gate same (polysilicon or polycrystalline adj silicon) same source same drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 16:36
	1	"6020600".PN.	USPAT	2003/02/12 16:13
	1	"5953602".PN.	USPAT	2003/02/12 16:13
	1	"5883399".PN.	USPAT	2003/02/12 16:14
	1	"5773343".PN.	USPAT	2003/02/12 16:14
	65	((257/329) or (257/330) or (257/332)).CCLS.) and trench near2 gate same (polysilicon or polycrystalline adj silicon) same source same drain and (epitaxial or epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 16:59
	4	((257/520) or (257/510) or (257/509) or (257/506) or (257/499)).CCLS.) and trench near2 gate same (polysilicon or polycrystalline adj silicon) same source same drain and (epitaxial or epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 17:04
	3	((257/520) or (257/510) or (257/509) or (257/506) or (257/499)).CCLS.) and trench near2 gate same (polysilicon or polycrystalline adj silicon) and (dmos or dmosfet).ti,ab. and (epitaxial or epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 17:06
	5	((257/520) or (257/510) or (257/509) or (257/506) or (257/499)).CCLS.) and trench and (polysilicon or polycrystalline adj silicon) and (dmos or dmosfet).ti,ab. and (epitaxial or epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 17:07
	93	trench and (polysilicon or polycrystalline adj silicon) and (dmos or dmosfet).ti,ab. and (epitaxial or epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 17:55
	2	("6124612").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 18:32
	452	(257/329).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 18:34
	3201	((257/520) or (257/509) or (257/510) or (257/506) or (257/499) or (257/329) or (257/330) or (257/332)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 18:53
	204	((257/520) or (257/509) or (257/510) or (257/506) or (257/499) or (257/329) or (257/330) or (257/332)).CCLS.) and (epitaxy or epitaxial or epitaxially) and (lateral or laterally) near12 (mos or dmos or nmos or pmos or cmos or mosfet or nmosfet or pmosfet or cmosfet or dmosfet or field adj effect or transistor) and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 18:57

	3	polysilicon near6 (sit shallow adj isolation adj trench) and (shallow adj trench adj isolation.ti.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/31 20:49
-	2	shallow adj trench adj isolation.ti. and polysilicon adj filling	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/31 20:54
-	0	deep adj trench adj isolation.ti. and polysilicon adj filling	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/31 20:54
-	0	deep adj trench adj isolation near20 polysilicon adj filling	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/31 20:54
-	14	deep adj trench adj isolation and polysilicon adj filling	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/31 21:00
-	2	("6339241").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/31 21:00
-	2	("5675173").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 12:07
-	2	deep adj trench adj isolation near3 bipolar.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 12:09
-	5	deep adj trench adj isolation near6 (mos mosfet nmos nmosfet pmos pmosfet bipolar).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 12:10
-	90	deep adj trench adj isolation.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 13:45
-	8	deep adj trench adj isolation and cmos and power.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 13:47
-	0	deep adj trench adj isolation near20 power adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 13:48
-	12	deep adj trench adj isolation and power adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 13:48
-	0	deep adj trench adj isolation and power adj transistor and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 14:49

-	300	power adj (device transistor) near20 (cmos cmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/01 14:51
-	117	power adj (device transistor) near3 (cmos cmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/01 14:51
-	35	power adj (device transistor) near3 (cmos cmosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/01 15:01
-	1	power adj (device transistor) near3 (cmos cmosfet).ti,ab,clm. and (latch-up or latchup)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/01 15:02
-	0	(i intrinsic) adj (znse zinc adj selenide) near6 conductivity adj type	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/04 16:34
-	151	photodiode.ti. and conductivity adj type.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/05 14:43
-	54	"4631803"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 10:54
-	2	("4631803").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/04 16:34
-	2	("5736445").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 11:04
-	6	((("4416050") or ("5476809") or ("5597742")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 11:36
-	1	((("4416050") or ("5476809") or ("5597742")).PN.) and surround\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 11:36
-	2306	((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/03 11:55
-	219	(guard adj ring guard-ring) and plan adj view and (dmos dmosfet bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/04 16:35
-	203	(guard adj ring guard-ring) and plan adj view and (dmos dmosfet bipolar adj transistor) and (power signal adj processing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/04 19:23

-	10	((("3500139") or ("4051506") or ("4261003") or ("4546370") or ("4725561") or ("4851078") or ("4860081") or ("4879584") or ("4897362") or ("4900689")).PN.	USPAT; IBM_TDB	2004/08/04 16:49
-	176	(guard adj ring guard-ring) and plan adj view and (dmos dmosfet bipolar adj transistor) and (power signal adj processing) and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 16:57
-	203	(guard adj ring guard-ring) and plan adj view and (dmos dmosfet bipolar adj transistor) and (power signal adj process\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 19:23
-	1171	(guard adj ring guard-ring trench groove) and plan adj view and (dmos dmosfet bipolar adj transistor) and (power signal adj process\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 19:24
-	1053	(guard adj ring guard-ring trench groove) and plan adj view and (dmos dmosfet bipolar adj transistor) and (power signal adj process\$3) and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 19:25
-	1053	(guard adj ring guard-ring trench groove) and plan adj view and (dmos dmosfet bipolar adj transistor) and (power signal adj process\$3) and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB	2004/08/04 19:26
-	502	(guard adj ring guard-ring isolation near3 (trench groove)) and plan adj view and (dmos dmosfet bipolar adj transistor) and (power signal adj process\$3) and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB	2004/08/04 19:32
-	320	(guard adj ring guard-ring isolation near3 (trench groove)) and plan adj view and (dmos dmosfet bipolar adj transistor) and epitax\$3 and (power signal adj process\$3) and (257/\$9.cccls. 438/\$9.cccls.)	USPAT; US-PGPUB	2004/08/04 19:34
-	0	(guard adj ring guard-ring isolation near3 (trench groove)) and plan adj view and (dmos dmosfet bipolar adj transistor) and epitax\$3 and (power signal adj process\$3) and (257/\$9.cccls. 438/\$9.cccls.) and ("N.sub.+ N.sub.-" "P.sub.+ P.sub.-")	USPAT; US-PGPUB	2004/08/04 19:35
-	0	(guard adj ring guard-ring isolation near3 (trench groove)) and plan adj view and (dmos dmosfet bipolar adj transistor) and epitax\$3 and (power signal adj process\$3) and (257/\$9.cccls. 438/\$9.cccls.) and ("N.sub.+" near2 "N.sub.-" "P.sub.+" near3 "P.sub.-")	USPAT; US-PGPUB	2004/08/04 19:37
-	4	899573.ap.	USPAT; US-PGPUB	2004/08/04 19:36
-	1	(guard adj ring guard-ring isolation near3 (trench groove)) and plan adj view and (dmos dmosfet bipolar adj transistor) and epitax\$3 and (power signal adj process\$3) and (257/\$9.cccls. 438/\$9.cccls.) and ("N+N-" "P+P-")	USPAT; US-PGPUB	2004/08/04 19:41
-	0	((guard adj ring guard-ring) near6 polysilicon) (isolation near3 (trench groove))) and plan adj view and (dmos dmosfet bipolar adj transistor) and epitax\$3 and (power signal adj process\$3) and (257/\$9.cccls. 438/\$9.cccls.) and ("N+N-" "P+P-")	USPAT; US-PGPUB	2004/08/04 19:42

-		0	((guard adj ring guard-ring) near8 polysilicon) (polysilicon near8 (isolation near3 (trench groove))) and plan adj view and (dmos dmosfet bipolar adj transistor) and epitax\$3 and (power signal adj process\$3) and (257/\$9.ccls. 438/\$9.ccls.) and ("N+N-" "P+P-")	USPAT; US-PGPUB	2004/08/04 19:43
-		1	((guard adj ring guard-ring) near8 polysilicon) (polysilicon near8 (trench groove)) and plan adj view and (dmos dmosfet bipolar adj transistor) and epitax\$3 and (power signal adj process\$3) and (257/\$9.ccls. 438/\$9.ccls.) and ("N+N-" "P+P-")	USPAT; US-PGPUB	2004/08/04 19:45
-		168	((guard adj ring guard-ring) near8 polysilicon) (polysilicon near8 (trench groove)) and plan adj view and (dmos dmosfet bipolar adj transistor) and epitax\$3 and (power signal adj process\$3) and (257/\$9.ccls. 438/\$9.ccls.) and ("N+N-" "P+P-")	USPAT; US-PGPUB	2004/08/04 19:56
-		37	((guard adj ring guard-ring) near8 polysilicon) (polysilicon near8 (trench groove)) near8 isolat\$3 and plan adj view and (dmos dmosfet bipolar adj transistor) and epitax\$3 and (power signal adj process\$3) and (257/\$9.ccls. 438/\$9.ccls.)	USPAT; US-PGPUB	2004/08/04 19:57

-	133	(US-6724043-\$ or US-6657242-\$ or US-6429502-\$ or US-6355537-\$ or US-6156622-\$ or US-6121102-\$ or US-6064106-\$ or US-5648283-\$ or US-5434447-\$ or US-5453640-\$ or US-5376822-\$ or US-5736445-\$ or US-6472709-\$ or US-5567634-\$ or US-4914058-\$ or US-4767722-\$ or US-4893160-\$ or US-5856701-\$ or US-6566223-\$ or US-6439514-\$ or US-6320233-\$ or US-6028344-\$ or US-6011297-\$ or US-5767578-\$ or US-5525824-\$ or US-4951102-\$).did. or (US-4835585-\$ or US-5773343-\$ or US-5814858-\$ or US-5689128-\$ or US-5298780-\$ or US-5034785-\$ or US-5818084-\$ or US-5319235-\$ or US-5583348-\$ or US-5644157-\$ or US-5770884-\$ or US-6184566-\$ or US-6335556-\$ or US-5675173-\$ or US-5920108-\$ or US-5668397-\$ or US-5909044-\$ or US-6204112-\$ or US-4631803-\$ or US-4916513-\$ or US-4922318-\$ or US-5059550-\$ or US-5159429-\$ or US-5221857-\$ or US-6133615-\$ or US-6239465-\$ or US-6184565-\$).did. or (US-5581110-\$ or US-5757081-\$ or US-5861330-\$ or US-5882966-\$ or US-5990537-\$ or US-5998822-\$ or US-4416050-\$ or US-5476809-\$ or US-5597742-\$ or US-6060731-\$ or US-6188104-\$ or US-6200841-\$ or US-6225659-\$ or US-6239464-\$ or US-6307231-\$ or US-6337499-\$ or US-6373098-\$ or US-6432775-\$ or US-6437390-\$ or US-6445037-\$ or US-6452230-\$ or US-6518127-\$ or US-5696010-\$ or US-5895951-\$ or US-5945708-\$ or US-6284604-\$ or US-6373097-\$).did. or (US-6118149-\$ or US-5986304-\$ or US-6288431-\$ or US-6396090-\$ or US-4661832-\$ or US-4933739-\$ or US-5969378-\$ or US-5917216-\$).did. or (US-20030203576-\$ or US-20030122154-\$ or US-20020085434-\$ or US-20040094819-\$ or US-20040097082-\$ or US-20040140503-\$ or US-20040089941-\$ or US-20040089942-\$ or US-20040089940-\$ or US-20040089925-\$ or US-20040070072-\$ or US-20040070060-\$ or US-20030227061-\$ or US-20030222304-\$ or US-20030207538-\$ or US-20030025164-\$ or US-20020179996-\$ or US-20020171118-\$ or US-20020014678-\$ or US-20010012655-\$ or US-20010050388-\$ or US-20010023961-\$ or US-20020121662-\$ or US-20020153557-\$ or US-20020158287-\$ or US-20030001199-\$).did. or (US-20020074585-\$ or US-20020179967-\$ or US-20020195653-\$ or US-20020038887-\$ or US-20030001202-\$ or US-20020100951-\$).did. or (EP-566186-\$ or EP-429131-\$ or EP-292972-\$ or EP-1193765-\$).did. or (JP-62065477-\$).did. or (JP-06334030-\$ or EP-509183-\$ or US-4416050-\$ or US-5665619-\$ or US-5243214-\$ or JP-63293938-\$ or US-20020038887-\$).did. or (NA85035501).tban.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 20:49
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-	9	((US-6724043-\$ or US-6657242-\$ or US-6429502-\$ or US-6355537-\$ or US-6156622-\$ or US-6121102-\$ or US-6064106-\$ or US-5648283-\$ or US-5434447-\$ or US-5453640-\$ or US-5376822-\$ or US-5736445-\$ or US-6472709-\$ or US-5567634-\$ or US-4914058-\$ or US-4767722-\$ or US-4893160-\$ or US-5856701-\$ or US-6566223-\$ or US-6439514-\$ or US-6320233-\$ or US-6028344-\$ or US-6011297-\$ or US-5767578-\$ or US-5525824-\$ or US-4951102-\$).did. or (US-4835585-\$ or US-5773343-\$ or US-5814858-\$ or US-5689128-\$ or US-5298780-\$ or US-5034785-\$ or US-5818084-\$ or US-5319235-\$ or US-5583348-\$ or US-5644157-\$ or US-5770884-\$ or US-6184566-\$ or US-6335556-\$ or US-5675173-\$ or US-5920108-\$ or US-5668397-\$ or US-5909044-\$ or US-6204112-\$ or US-4631803-\$ or US-4916513-\$ or US-4922318-\$ or US-5059550-\$ or US-5159429-\$ or US-5221857-\$ or US-6133615-\$ or US-6239465-\$ or US-6184565-\$).did. or (US-5581110-\$ or US-5757081-\$ or US-5861330-\$ or US-5882966-\$ or US-5990537-\$ or US-5998822-\$ or US-4416050-\$ or US-5476809-\$ or US-5597742-\$ or US-6060731-\$ or US-6188104-\$ or US-6200841-\$ or US-6225659-\$ or US-6239464-\$ or US-6307231-\$ or US-6337499-\$ or US-6373098-\$ or US-6432775-\$ or US-6437390-\$ or US-6445037-\$ or US-6452230-\$ or US-6518127-\$ or US-5696010-\$ or US-5895951-\$ or US-5945708-\$ or US-6284604-\$ or US-6373097-\$).did. or (US-6118149-\$ or US-5986304-\$ or US-6288431-\$ or US-6396090-\$ or US-4661832-\$ or US-4933739-\$ or US-5969378-\$ or US-5917216-\$).did. or (US-20030203576-\$ or US-20030122154-\$ or US-20020085434-\$ or US-20040094819-\$ or US-20040097082-\$ or US-20040140503-\$ or US-20040089941-\$ or US-20040089942-\$ or US-20040089940-\$ or US-20040089925-\$ or US-20040070072-\$ or US-20040070060-\$ or US-20030227061-\$ or US-20030222304-\$ or US-20030207538-\$ or US-20030025164-\$ or US-20020179996-\$ or US-20020171118-\$ or US-20020014678-\$ or US-20010012655-\$ or US-20010050388-\$ or US-20010023961-\$ or US-20020121662-\$ or US-20020153557-\$ or US-20020158287-\$ or US-20030001199-\$).did. or (US-20020074585-\$ or US-20020179967-\$ or US-20020195653-\$ or US-20020038887-\$ or US-20030001202-\$ or US-20020100951-\$).did. or (EP-566186-\$ or EP-429131-\$ or EP-292972-\$ or EP-1193765-\$).did. or (JP-62065477-\$).did. or (JP-06334030-\$ or EP-509183-\$ or US-4416050-\$ or US-5665619-\$ or US-5243214-\$ or JP-63293938-\$ or US-20020038887-\$).did. or (NA85035501).tban.) and (dmos dmosfet) and bipolar adj transistor and ((trench near8 isolat\$3) guard adj ring) and (epitaxial epitaxially epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/04 20:51
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